

# FDC6392S

## 20V Integrated P-Channel PowerTrench® MOSFET and Schottky Diode

### General Description

The FDC6392S combines the exceptional performance of Fairchild's PowerTrench MOSFET technology with a very low forward voltage drop Schottky barrier rectifier in an SSOT-6 package.

This device is designed specifically as a single package solution for DC to DC converters. It features a fast switching, low gate charge MOSFET with very low on-state resistance. The independently connected Schottky diode allows its use in a variety of DC/DC converter topologies.

### Features

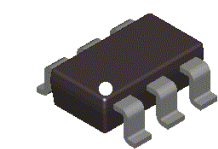
#### MOSFET:

- -2.2 A, -20V.  $R_{DS(ON)} = 150\text{ m}\Omega @ V_{GS} = -4.5\text{V}$   
 $R_{DS(ON)} = 200\text{ m}\Omega @ V_{GS} = -2.5\text{V}$
- Low Gate Charge (3.7nC typ)

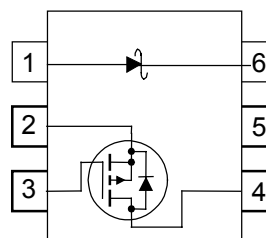
- Compact industry standard SuperSOT™-6 package

#### Schottky:

- $V_F < 0.45\text{ V} @ 1\text{ A}$



Pin 1  
**SuperSOT™-6**



### Absolute Maximum Ratings T<sub>A</sub>=25°C unless otherwise noted

Symbol	Parameter	Ratings	Units
V <sub>DSS</sub>	MOSFET Drain-Source Voltage	-20	V
V <sub>GSS</sub>	MOSFET Gate-Source Voltage	±12	V
I <sub>D</sub>	Drain Current – Continuous (Note 1a)	-2.2	A
	– Pulsed	-6	
P <sub>D</sub>	Power Dissipation for Single Operation (Note 1a)	0.96	W
	(Note 1b)	0.9	
	(Note 1c)	0.7	
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C
V <sub>RRM</sub>	Schottky Repetitive Peak Reverse Voltage	20	V
I <sub>O</sub>	Schottky Average Forward Current (Note 1a)	1	A

### Thermal Characteristics

R <sub>θJA</sub>	Thermal Resistance, Junction-to-Ambient (Note 1a)	130	°C/W
R <sub>θJC</sub>	Thermal Resistance, Junction-to-Case (Note 1)	60	

### Package Marking and Ordering Information

Device Marking	Device	Reel Size	Tape width	Quantity
.392	FDC6392S	7"	8mm	3000 units

**Electrical Characteristics** $T_A = 25^\circ\text{C}$  unless otherwise noted

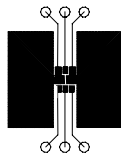
Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
<b>Off Characteristics</b>						
$BV_{DSS}$	Drain–Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = -250\ \mu\text{A}$	-20			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		-16		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = -16\text{ V}, V_{GS} = 0\text{ V}$			-1	$\mu\text{A}$
$I_{GSSF}$	Gate–Body Leakage, Forward	$V_{GS} = 12\text{ V}, V_{DS} = 0\text{ V}$			100	nA
$I_{GSSR}$	Gate–Body Leakage, Reverse	$V_{GS} = -12\text{ V}, V_{DS} = 0\text{ V}$			-100	nA
<b>On Characteristics (Note 2)</b>						
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_D = -250\ \mu\text{A}$	-0.6	-1.0	-1.5	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate Threshold Voltage Temperature Coefficient	$I_D = -250\ \mu\text{A}$ , Referenced to $25^\circ\text{C}$		3		mV/ $^\circ\text{C}$
$R_{DS(on)}$	Static Drain–Source On–Resistance	$V_{GS} = -4.5\text{ V}, I_D = -2.2\text{ A}$ $V_{GS} = -2.5\text{ V}, I_D = -1.8\text{ A}$ $V_{GS} = -4.5\text{ V}, I_D = -2.2\text{ A}, T_J = 125^\circ\text{C}$		101 152 132	150 200 211	m $\Omega$
$I_{D(on)}$	On–State Drain Current	$V_{GS} = -4.5\text{ V}, V_{DS} = -5\text{ V}$	-6			A
$g_{FS}$	Forward Transconductance	$V_{DS} = -5\text{ V}, I_D = -2.2\text{ A}$		6		S
<b>Dynamic Characteristics</b>						
$C_{iss}$	Input Capacitance	$V_{DS} = -10\text{ V}, V_{GS} = 0\text{ V},$ $f = 1.0\text{ MHz}$		369		pF
$C_{oss}$	Output Capacitance			80		pF
$C_{rss}$	Reverse Transfer Capacitance			39		pF
$R_G$	Gate Resistance	$V_{GS} = -15\text{ mV}, f = 1.0\text{ MHz}$		7.6		$\Omega$
<b>Switching Characteristics (Note 2)</b>						
$t_{d(on)}$	Turn–On Delay Time	$V_{DD} = -10\text{ V}, I_D = -1\text{ A},$ $V_{GS} = -4.5\text{ V}, R_{GEN} = 6\ \Omega$		8	16	ns
$t_r$	Turn–On Rise Time			11	20	ns
$t_{d(off)}$	Turn–Off Delay Time			13	23	ns
$t_f$	Turn–Off Fall Time			4	8	ns
$Q_g$	Total Gate Charge	$V_{DS} = -10\text{ V}, I_D = -2.2\text{ A},$ $V_{GS} = -4.5\text{ V}$		3.7	5.2	nC
$Q_{gs}$	Gate–Source Charge			1		nC
$Q_{gd}$	Gate–Drain Charge			1		nC
<b>Drain–Source Diode Characteristics and Maximum Ratings</b>						
$I_S$	Maximum Continuous Drain–Source Diode Forward Current				-0.8	A
$V_{SD}$	Drain–Source Diode Forward Voltage	$V_{GS} = 0\text{ V}, I_S = -0.8\text{ A (Note 2)}$		-0.8	-1.2	V
$t_{rr}$	Diode Reverse Recovery Time	$I_F = -2.2\text{ A},$ $dI_F/dt = 100\text{ A}/\mu\text{s}$		5.4		nS
$Q_{rr}$	Diode Reverse Recovery Charge			1.2		nC
<b>Schottky Diode Characteristics</b>						
$I_R$	Reverse Leakage	$V_R = 20\text{ V}$	$T_J = 25^\circ\text{C}$	148	400	$\mu\text{A}$
			$T_J = 100^\circ\text{C}$	14	20	mA
		$V_R = 10\text{ V}$	$T_J = 25^\circ\text{C}$	55	200	$\mu\text{A}$
			$T_J = 100^\circ\text{C}$	5.2	10	mA
$V_F$	Forward Voltage	$I_F = 500\text{ mA}$	$T_J = 25^\circ\text{C}$	0.34	0.4	V
			$T_J = 100^\circ\text{C}$	0.26	0.35	
		$I_F = 1\text{ A}$	$T_J = 25^\circ\text{C}$	0.40	0.45	V
			$T_J = 100^\circ\text{C}$	0.35	0.42	

## Electrical Characteristics

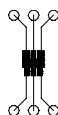
$T_A = 25^\circ\text{C}$  unless otherwise noted

**Notes:**

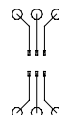
1.  $R_{\theta JA}$  is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



- a)  $130^\circ\text{C/W}$  when mounted on a  $0.125\text{ in}^2$  pad of 2 oz. copper.



- b)  $140^\circ\text{C/W}$  when mounted on a  $.004\text{ in}^2$  pad of 2 oz copper



- c)  $180^\circ\text{C/W}$  when mounted on a minimum pad.

Scale 1 : 1 on letter size paper

2. Pulse Test: Pulse Width  $< 300\mu\text{s}$ , Duty Cycle  $< 2.0\%$

### Typical Characteristics

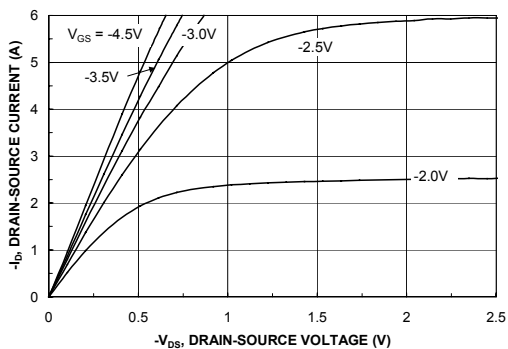


Figure 1. On-Region Characteristics.

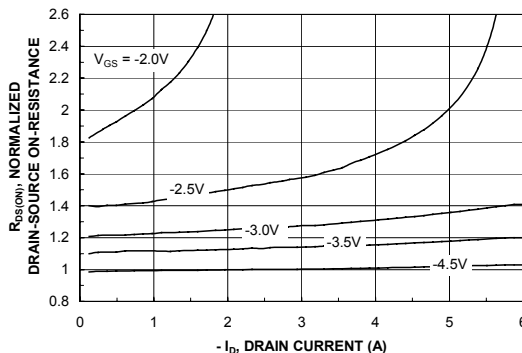


Figure 2. On-Resistance Variation with Drain Current and Gate Voltage.

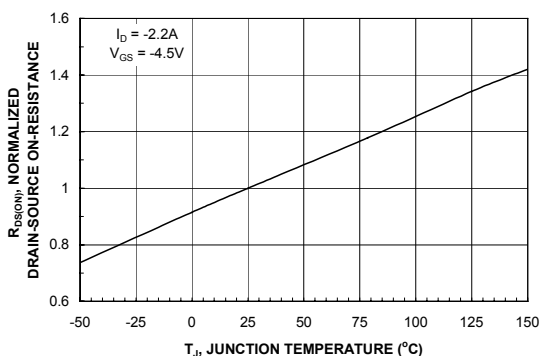


Figure 3. On-Resistance Variation with Temperature.

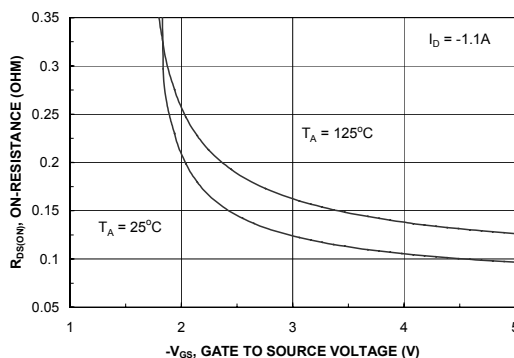


Figure 4. On-Resistance Variation with Gate-to-Source Voltage.

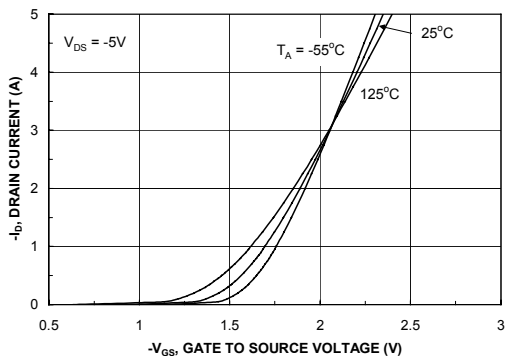


Figure 5. Transfer Characteristics.

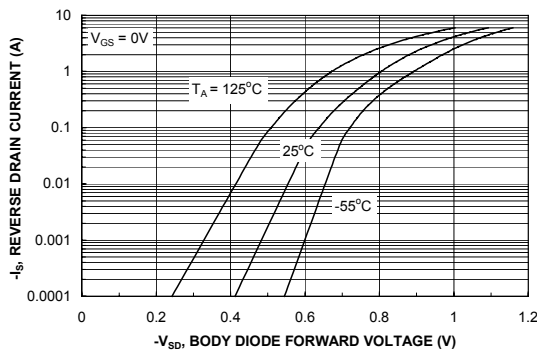


Figure 6. Body Diode Forward Voltage Variation with Source Current and Temperature.

### Typical Characteristics

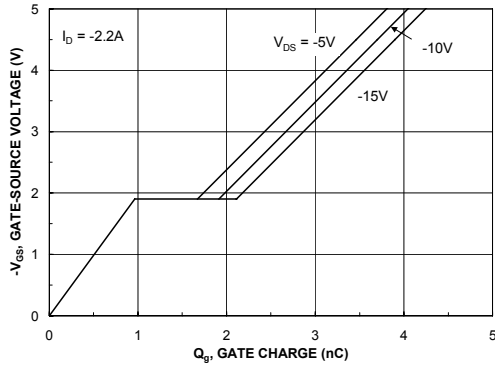


Figure 7. Gate Charge Characteristics.

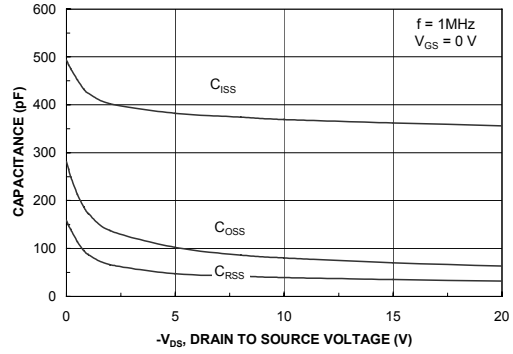


Figure 8. Capacitance Characteristics.

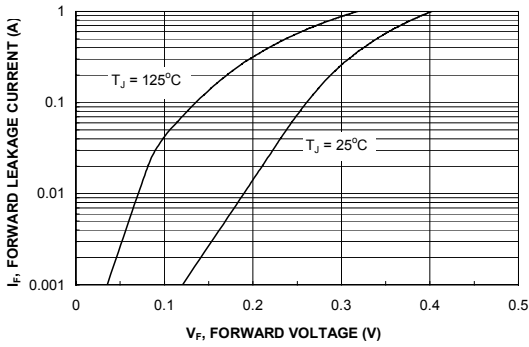


Figure 9. Schottky Diode Forward Voltage.

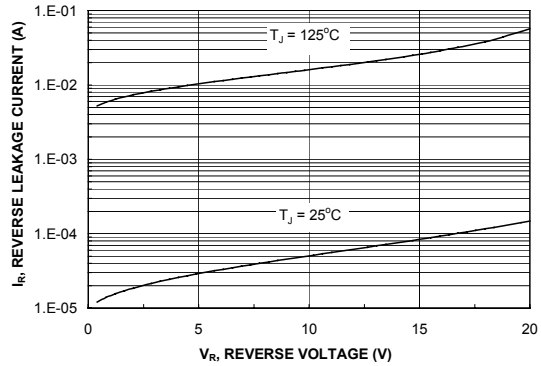


Figure 10. Schottky Diode Reverse Current.

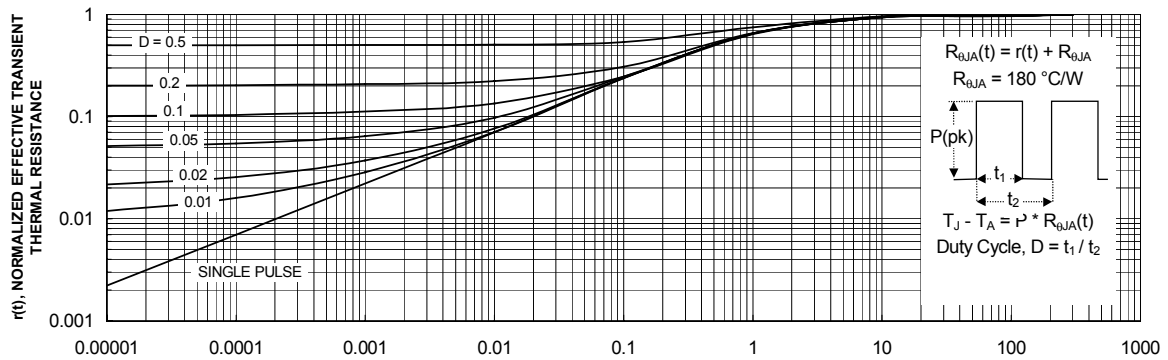


Figure 11. Transient Thermal Response Curve.

Thermal characterization performed using the conditions described in Note 1c.  
 Transient thermal response will change depending on the circuit board design.

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